

Index

Note: Page numbers in *italics* refers to figures.

a

acoustochemical method 203, 206
alkanethiol-coated gold nanocrystals 59
 α -selenium 199
anisotropy
 of BP 147–148
 of electron transport in 2D tellurium
 nanosheets 181
 of probe sonications 213
 of selenium 199, 211
 of tellurium 172
 of *t*-Se 206
antimonene 231
 preparation of 241–242
 properties and applications of 242–244
arc discharge (AD) 10, 11–12
arsenene 231–232
 preparation of 241–242
 properties and applications of 242–244
atomic force microscopy (AFM) 174,
 200–201
atomic layer deposition (ALD) 70, 151
Au-Si binary phase diagram 47

b

ballistic transport mechanism 78–79
ball milling method 17, 141
bandgap shift in Si NWs 77
batteries 189–190
 Li-Te and Te-Al 190
 lithium 71

 silicon-based lithium 72
 tellurium NWs 189–190
Bessel factor of Si NWs 74
 β -selenium 199
bilayer graphene (BLG) 9
 twisted 23
biomedical and sensing 155
black phosphorus (BP) 139, 145, 153,
 154, 175
 anisotropy of 147–148
 applications of 148
 ball milling 141
 in biomedical and sensing 155–157
 bottom-up approach 144–146
 energy band structure of 147
 field effect transistor 152–153
 high pressure 140–141
 lattice structure of 146–147
 mineralization 141–142
 nanosheets, synthesis of 142
 in photocatalytic degradation 157–158
 in photodetector 148–152
 properties of 146
 solar cell 153–155
 synthesis of 139
 top-down approach 142–144
black phosphorus quantum dots
 (BPQDs) 155–157, 156
blown bubble film (BBF) method 62
blue phosphorus 159, 159
borophene 231, 232

borophene (*continued*)
 preparation of 232–234
 properties and applications of 234–237
 Bosch process 91, 93
 bottom-up methods 2, 8–9. *see also*
 top-down method
 of BP nanosheets 144
 chemical vapor deposition 144–145
 elementary substances of 1
 etching methods 42
 fabrication of 2
 of graphene 8–9
 for in-plane FET implementations 86
 nanomaterials 1
 for preparing borophene 233
 properties and applications of 17–25
 for Si NWs 77, 84
 solvothermal method 146

C

carbon (C) 1
 for synthesizing selenium
 nanostructures 199
 carbon nanotubes (CNT) 1, 9
 arc discharge 11–12
 chemical vapor deposition 12
 graphyne 13–17
 laser ablation 12
 properties and applications of 25–29
 types 10
 carbon nanotubes field effect transistors
 (CNT-FETs) 12
 carbon-thermal chemical vapor deposition
 method 203
 catalysts 42, 47
 Au 118, 119
 B-type 41
 downscaling strategies 61
 droplets 44, 44
 Fe 58, 59
 formed using pre-patterned layers 45
 metal 12, 45, 46
 non-Au 47
 precursor 13
 residual 12

structure and components of 13
 TEM image of SWCNTs with marked 12
 transition metal 10
 type A gold catalysts 49–50
 type B low Si solubility catalysts 50–51
 type C silicide-forming catalysts 51
 VLS 45
 cetyltrimethylammonium bromide
 (CTAB) 203
 chemical template method 187–189
 chemical vapor deposition (CVD) 2, 9, 42,
 116–118, 175
 borophene preparation using 233
 of BP nanosheets 144–145
 carbon-thermal 203
 of CNT 12–13
 floating catalyst 13
 for GDY synthesis 17, 17
 graphene 17
 PECVD 70
 preparing photovoltaic NW arrays 71
 pulsed plasma-enhanced 51
 schematic of low-temperature 46
 silane 42, 51
 substrate-supported catalyst 12
 tetrachlorosilane 42
 chemical vapor transport (CVT) 145
 BP prepared by 157
 violet phosphorus synthesized
 using 160
 Chern insulator (CI) 23
 chirality 177
 chiral tellurium nanomaterials, synthesis
 of 177–179
 chitosan (CS) 208
 CO₂ reduction reaction (CO₂RR) 157
 cocoa bean shell extract (CBSE) 201
 complementary metal oxide semiconductor
 (CMOS) 41
 initiating pace of “Very Large Scale
 Integration,” 80
 JNTs compatible with 81
 Si NW fabrication process with 76
 SOI NWs fabricated using 84
 conduction bands (CBs) 149

confinement-controlled sublimation
(CCS) 2, 8

contact gate pitch (CGP) 27

contact printing 44, 62

conventional mechanical stripping
techniques 142–143

conventional MOSFETs 76

Coulombic efficiency 125, 126

Cowley's theory 123

cyclic voltammetry 189

d

deep reactive ion etching (DRIE) 60

dielectrophoresis (DEP) 61

of NWs 61–62

differential web printing method 62

dimethylformamide (DMF) 143

diphenylsilane (DPS) 42

dissolution-based methods 41, 59–60

drain-induced barrier lowering (DIBL) 76

dry exfoliation of graphene 3

dynamic random access memory (DRAM) 84

Si NW-implemented SRAM and DRAM 85

e

E-beam lithography (EBL) 60

electrochemical exfoliation (ECE) 5–6

electrochemical method 217

electrochemical stripping method 143

electronics

BP in 111

fabrication of Si NW transistors 85–94

germanium nanowires in 111

micro 9

properties 77–80

selenium in 216–219

Si NW-based field effect transistors 80–85

electron transport in Si NWs 77

energy band structure of BP 147

energy dispersive spectrometer (EDS) 43

energy storage

applications of Ge nanomaterials 124–128

batteries as 189–190

borophene in 234

BP in 148

and conversion of selenium

nanostuctures 219

and conversion of solar cells 219

germanium nanowires 111

epitaxial graphene on silicon carbide 8

epitaxial growth strategy 241

etching methods 42, 60–61, 73

dry etching 60, 181

metal-assisted chemical etching 60–61

reactive ion etching 60

for Si NWs 71

exfoliated tellurium nanosheets 177

extreme ultraviolet (EUV) patterning 88

f

fabrication of Si NW transistors 86

3D-stacked Si NWs 88–94, 92–93

gate-all-around nanowire

transistor 87–88

Si NW Plainar transistor 86–87

fast Fourier transform (FFT) 179

feedback effect of weak shock ionization

(FBFET) 85

femtosecond pump-probe ultraviolet

photoelectron spectroscopy

(fs-UPS) 219

few-layer graphene (FLG) 3, 3, 150, 151

field effect transistors (FETs) 43, 111, 142,

217, 231

BP nanosheets and 152–153

carbon nanotubes 12

conventional

metal-oxide semiconductor 76

fabrication of Si NW transistors 86–94

FinFETs 76

germanium and 128–130

graphene 18

inversion-mode

metal-oxide-semiconductor 80

junctionless 76, 81

memory 85

negative capacitance 80

NW transistors beyond Boltzmann 84–85

reconfigurable NW FETs 82–83

Schottky barrier field effect transistors 82

- field effect transistors (FETs) (*continued*)
 - Si NW-based field effect transistors 80
 - Si NW-implemented SRAM and DRAM 85
 - Si NW single-electron field effect transistors and Si NW quantum dots 83–84
 - Si-P-channel metal oxide semiconductor 27
 - tellurium NWs 171
 - tunnelling 80
- field-effect tunnelling transistors (FETTs) 18
- field-emission scanning electron microscopy (FESEM) 206
- Fin field-effect transistor (FinFETs) 76
- floating catalyst CVD (FCCVD) 13
- fluid alignment strategy 61
- fluorine-doped tin oxide (FTO) 219
- fullerenes 1, 2, 10, 11
- g**
 - gas–liquid–solid (VLS) mechanisms 12, 71, 73, 116, 118, 199
 - gas-phase deposition 175, 207
 - gas sensing 186–187
 - gate-all-around FET (GAA FET) 76
 - gate-all-around nanowire transistor 87–88
 - gate-all-around silicon nanowire transistor (GAA SNWT) 88–89, 89
 - gated NW resistors. *see* junctionless transistors (JLTs)
 - Ge NPs 125
 - germanium (Ge) 111
 - chemical vapor deposition 116–118
 - energy storage applications 124–128
 - field effect transistor 128–130
 - hydrothermal synthesis 118–120
 - laser ablation 112–113
 - nanomaterials, synthesis of 112
 - optical properties 120–122
 - properties and applications of 120
 - Raman spectrum 122–123, 124
 - SFLS method 113–115
 - thermal evaporation method 115–116
 - germanium nanowires (Ge NWs) 111, 115, 116, 118, 119
 - gate allosteric field effect transistor 130
 - preparation 112
 - graphdiyne (GDY) 13, 30
 - graphene 1, 2, 231
 - bottom-up methods 8–9
 - electrical properties and applications 18–20
 - graphene-like elements 231
 - layer 11
 - monolayers 1
 - nonlayered Se nanosheets 212
 - optoelectronic properties and applications 20–23
 - properties and applications of 17–18
 - relationship between other carbon nanostructures and 2
 - spintronic properties 23
 - superconductive properties 23
 - top-down methods 3–7
 - graphene field effect transistors (GFETs) 18
 - graphene nanoribbons (GNRs) 1
 - graphene oxide (GO) 2
 - graphene strain-effect transistor (GSET) 18, 19
 - graphene-WS₂-graphene (GWG) 18
 - graphite 1, 2, 11
 - graphyne (GY) 1, 13
 - containing different numbers of inserted acetylene bonds 14
 - liquid-phase synthesis 15–16
 - properties and applications of 30
 - solid-phase synthesis 17
 - growth-assembly methods 61
 - blown bubble film method 62
 - dielectrophoresis of NWs 61–62
 - fluid alignment strategy 61
 - Langmuir–Blodgett assembly strategy 61
 - printing 62
- h**
 - hexaethylbenzene (HEB) 15, 17
 - high-angle annular dark-field scanning transmission electron microscopy (HAADF-STEM) 172
 - high pressure method 140–141

high-resolution transmission electron
microscopy (HRTEM) 112, 170, 206,
233–234
Hittorf's phosphorus. *see* violet phosphorus
horizontal Si NWs 61
growth-assembly methods 61–62
in situ growth of lateral NWs 62–63
hybrid C-FinFET common-source amplifier
(H-CA) 81
hydrothermal method 146, 187
hydrothermal synthesis method 119–120,
175–177, 201

i

in-plane solid–liquid–solid (IPSLS)
method 41, 62
in situ growth of lateral NWs 62–63
internal quantum efficiency (IQE) 67
Internet of Things (IoT) 76

j

junctionless accumulation mode field
effect transistors (JAM FETs). *see*
junctionless transistors (JLTs)
junctionless field effect transistor (JL-FETs).
see junctionless transistors (JLTs)
junctionless nanowire transistor (JNT) 81
junctionless transistors (JLTs) 80, 81

l

Langmuir–Blodgett assembly strategy 61
large-scale integration (LSI) 76
laser ablation (LA) 10, 12, 55, 62, 112–113, 202
pulsed 201
layer-antiferromagnetic insulator (LAF
insulator) 23
layer-by-layer sequential stacked NW
transistor 89–91
layer-engineered exfoliation (LEE) 3
layer-polarized insulator (LPI) 23
liquid nitrogen-assisted green stripping
method 158
liquid-phase exfoliation 2, 177
for biomedical applications 240
of graphene 4–5

selenium nanosheets preparation using 211
tellurium nanosheets by 186
liquid-phase stripping method 144, 177
liquid-phase synthesis of graphyne 15–16
lithium
lithium-ion batteries 189
reversible precipitation of 125
Si NW-based anode materials for lithium
batteries 71–73

m

magic-angle tBG (MATBG) 24
mechanical exfoliation method 142–143
Meiners effect 239
metal-assisted chemical etching (MACE)
method 41, 42, 60–61
metal catalysts 10, 47
classified according to binary phase
diagram 47
diffusion of 46
metal-catalyst-Si clusters 42
physical state of 12
pre-deposition 13
types of 45
metal NPs 42, 43
process of patterning 44–45
metal-oxide-semiconductor field effect
transistors (MOSFETs) 76
metamaterial integration strategy 21
micromechanical cleavage method 2
microwave-assisted method 201
Mie theory 122
mineralization 141–142
molecular beam epitaxy (MBE) 45, 233, 237
monolayer graphene (MLG) 9
monophenylsilane 42
Moore's Law 41, 76, 175
multigate FETs 76
multi-walled carbon nanotubes
(MWCNTs) 10, 11

n

nanocrystalline silicon (i-nc-Si) 67
nanocrystals
germanium 118, 120

- nanocrystals (*continued*)
 - gold 114
 - Ni 115
 - tellurium 169
 - nanomaterials 111, 170, 199
 - nanoparticles (NPs) 42, 115, 156
 - Ag 60
 - atomic force microscopy images of 200–201
 - Au 45, 115–116
 - Bi 51
 - Ge 117, 118, 124–125
 - metal 42, 45
 - porous 126
 - selenium 60, 200, 202, 222
 - tellurium 170, 179
 - Zn-BPQDs 156
 - nanoribbon 174, 213
 - controlled synthesis of tellurium 174
 - graphene 1
 - t*-Se 215
 - nanotechnology 199
 - using open-source tools 83
 - nanotubes
 - boron nitride 172
 - carbon 9–17, 172
 - controlled synthesis of tellurium 172–173
 - one-dimensional 2
 - in semiconductors and energy storage
 - devices 170
 - single-walled 172
 - synthesis of selenium 206–208
 - TEM images of 207, 207
 - nanowire field effect transistor (NWFET) 130
 - nanowires (NWs) 41, 169
 - 1D selenium 200
 - 3D-stacked Si NWs 88, 92–93
 - circuit 62
 - controlled synthesis of tellurium 171–172
 - dielectrophoresis of 61–62
 - synthesis 42
 - transistors beyond Boltzmann 84–85
 - vertically stacked multi-NWs by
 - etching 91–94
 - ZnO 152
 - near-infrared (NIR) laser irradiation 153, 241
 - negative capacitance field effect transistors (NCFETs) 80
 - nitrogen reduction reaction (NRR) 157
 - N*-methylpyrrolidone (NMP) 144, 177
 - noise equivalent power (NEP) 22–23
 - nonvolatile memory (NVM) 85
- O**
- optical trapping, Si NW arrays for 64–67
 - optoelectronics
 - graphene in 20
 - selenium in 216–219
 - ORADEP 91
 - Oriented Attachment (OA) 41
 - Oswald maturation 45
 - oxide-assisted growth (OAG) 42, 55
 - characterization of OAG NWs 57
 - development of 55
 - growth on substrate 57–58
 - precursor states in heat pipes 55–57
- P**
- passivation of Si NW solar cells 69–71
 - patterning metal NPs process 44–45
 - phase diagrams of metal-Si systems 47–48, 48
 - phosphorene 231
 - phosphorus
 - black 139–158
 - blue 159
 - violet 160–161
 - photocatalytic degradation 157–158
 - photocatalytic hydrogen evolution reaction (HER) 157
 - photocatalytic nitrogen reduction
 - reaction 157
 - photodetectors (PDs) 20, 148–152, 171, 216
 - photoelectrochemical (PEC) biosensor 155
 - photoluminescence (PL) 120, 215–216
 - physical vapor deposition (PVD) 175, 218
 - plasma-enhanced chemical vapor deposition (PPECVD) 51
 - polydimethylsiloxane (PDMS) 149

polymethylmethacrylate (PMMA) 149
 poly(triarylamine) (PTAA) 155
 polyvinylpyrrolidone (PVP) 177
 porous anodic alumina (PAA) 44
 power conversion efficiency 219
 projected density of states (PDOS) plot 240
 propylene carbonate (PC) 143
 pulsed laser ablation method 201–202

q

quantum anomalous Hall effect (QAHE) 23
 quantum confinement effects (QCE) 80
 quantum dots, Si NW 83–84
 quasi-equilibrium annealing method 8

r

radial junctions in Si NWs 67
 Raman spectra
 of 0D amorphous selenium NPs 215
 of 2D Se nanosheet 215
 of antimonene 243, 244
 of arsenene 242, 243
 of borophene 234, 235
 BP nanosheets using 143
 of germanium 122–123, 124
 of HCDG and pristine graphite 7
 of selenium nanostructures 214–215
 reactive ion etching (RIE) method 60
 reconfigurable field effect transistors
 (RFETs) 80
 reconfigurable NW FETs 82–83
 red phosphorus (RP) 139
 reduced graphene oxide (rGO) 6, 7
 resistive interfacial layer deposition
 technique 217

s

scanning electron microscopy (SEM) 43,
 116, 208, 232
 of aligned CNT PD 28
 of borophene 232, 233
 of GDY 16
 of Ge nanostructures 117
 of Ge NWs 115, 116, 118, 119
 of NWs 116, 119

 of planar n-i-p chalcogenide solar
 cell 154
 of selenium rods 209
 of Si NWs 46
 of strain-induced nanogap across Ni/Au
 contact 19
 of tellurium nanotubes 173
 of three top-gated CNT-FETs 27
 of vertically stacked multi-NWs 92
 Schottky barrier field effect transistors
 (SBFETs) 76, 82
 Schottky barrier height (SBH) 82
 Seebeck effect 73
 selected area electron diffraction
 (SAED) 172
 of ABC-stacked GDY 15
 of AgSeTe NWs 188, 188
 of HCDG basal plane 7
 pattern of GDY 16
 selenium 199
 0D selenium nanostructures 200–203
 1D selenium nanostructures 203–211
 2D selenium nanostructures 211
 AFM image of selenium NPs 202
 nanomaterials, synthesis of 200
 selenium nanorods (Se-NRs) 208
 anticancer properties of synthesized 220
 effect on viability of Hep-G2 and MCF-7
 human cancer cells 221
 FESEM image of 209
 inhibitory effect of 220
 synthesis of 208–209
 selenium nanostructures
 1D selenium nanostructures 203–211
 biological applications 220–222
 electronics/optoelectronics 216–219
 energy storage and conversion 219
 optical properties 213–214
 photoluminescence 215–216
 properties and applications of 212
 Raman spectroscopy 214–215
 selenium nanobelts synthesis 209–211
 selenium nanorods synthesis 208–209
 selenium nanotubes synthesis 206–208
 selenium NWs, synthesis of 203–206

- self-assembled layer exfoliation patterning
 - method 45
- self-selected orbital coupling (SOC) 231
 - in graphene 23
 - proximity-induced 23
 - of stanene 239, 239
- semiconductor epigraphene (SEG) 8
 - characterization of 8
 - intrinsic transport properties on SiC 20
 - p-doped 20
- short-channel effects (SCE) 41, 76
 - FinFETs suffer from 88
 - gate-all-around nanowire transistor for 87
 - NCL scheme for 88
 - vacuum dielectric structures for 81
- silane chemical vapor deposition 42
- silicon carbide, epitaxial graphene on 8
- silicon nanowires (Si NWs) 41
 - applications of 41, 63
 - arrays for optical trapping 64–67
 - dissolution-based methods 59–60
 - electronics of Si NWs 76–94
 - etching methods 60–61
 - fundamental aspects and morphology
 - analysis of VLS growth 43–51
 - horizontal Si NWs 61–63
 - morphology analysis for VLS or VSS
 - methods 51–54
 - oxide-assisted growth 55–58
 - passivation of Si NW solar cells 69–71
 - principle and structure of 64
 - radial junctions in Si NWs 67
 - Si NW-based anode materials for lithium
 - batteries 71–73
 - solar cell performance
 - improvements 67–69
 - synthesis of 42
 - thermal annealing of silicon
 - substrates 58–59
 - thermoelectric generators 73–76
- silicon-on-insulator (SOI) 80
- silicon transportation process 45–46
- simple single-step synthesis method 124
- single-electron field effect transistors, Si
 - NW 83–84
- single-electron transistors (SETs) 80
- single-walled carbon nanotubes
 - (SWCNTs) 10, 172
 - aerogel 189
 - functionalized 189
 - laser ablation 12
 - relative junction conductance of 26
 - semiconductive 25–26
 - single-chirality SWCNT solutions 26, 26
 - TEM image with marked catalyst 12
 - type II 26
 - in unfolded 2D graphene layer 11
- Si-P-Channel Metal Oxide Semiconductor
 - Field Effect Transistors
 - (PMOSFETs) 27
- solar cell 219, 220
 - BP for 153–155
 - passivation of Si NW 69–71
 - performance improvements 67–69
 - principle and structure of Si NW 64–67
 - Si NW 63, 65–66
 - Sn for 51
- solid–liquid–solid (SLS) method 42, 60, 199
 - precursor states in heat pipes 55–57
- solid-phase synthesis of graphyne 17
- solid–solution–solid growth mechanism 207
- solvation conjugation mechanism 157
- solvothermal method 146
- spin-on doping (SOD) technique 75
- spin-orbit coupling (SOC) 23
 - in silicon 84
 - in tellurium 169, 179, 184
- stanene 231–232, 237
 - preparation of 237–238
 - properties and applications of 238
- Staphylococcus aureus* 221
- static random access memory (SRAM) 27
 - 6T SRAM 81
 - Si NW-implemented SRAM and
 - DRAM 85
- steel gallium-zinc oxide (InGaZnO) 153
- substrate-supported catalyst CVD
 - (SCCVD) 12
 - metal catalyst pre-deposition in 13
- supercritical carbon dioxide (SCCO₂) 4

- supercritical flow–solid–solid (SFSS)
 - method 115
- supercritical fluid (SCF) 4
- supercritical fluid–liquid–solid (SFLS)
 - method 42, 113–115
- t**
- Tafel slope 234–235
- tangential stress 5
- tellurene 176
- tellurium (Te) 169
 - chiral tellurium nanomaterials, synthesis
 - of 177–179
 - nanomaterials, controlled synthesis
 - of 170–179
- tellurium–aluminum battery (TAB) 189
- tellurium nanostructures
 - 1D 170–174
 - 2D 175–177
 - batteries 189–190
 - chemical templates 187–189
 - chiral properties 184–186
 - electrical property 179–181
 - gas sensing 186–187
 - photoconductive properties 181–183
 - piezoelectric thermoelectric
 - properties 183–184
 - properties and applications of 179
- template method 125
- tetrachlorosilane CVD 42
- thermal annealing of silicon
 - substrates 58–59
- thermal evaporation method 115–116
- thermoelectric generators (TEGs) 73
 - on-chip integration of Si NW-based
 - thermoelectric modules 76
 - Si NW-based TEGs 74–76
- time-of-flight technique 217
- top-down method 2, 199. *see also* bottom-up
 - methods
 - of BP nanosheets 142–144
 - etching methods 42
 - of graphene 3–6, 7
 - in-plane FET implementations based on 86
 - in Si NW technology 84
- transfer printing (TP) 62
- transmission electron microscopy
 - (TEM) 43, 170, 200, 232
 - of antimonene 241
 - of arsenene 242
 - of as-prepared 2D nonlayered Se
 - nanosheets 212
 - of borophene 232, 233
 - BP nanosheets using 143
 - of eight MSeTe 189
 - of germanium nanowires 111, 113, 114, 127
 - of Ge single-crystal quantum wire 114
 - image of MWCNTs 11
 - of NPs 201
 - of selenium nanostructures 200
 - of selenium nanotubes 206, 207
 - of selenium NP 202, 203
 - of Se nanobelts 210
 - of Se NWs 204, 205, 205
 - of SWCNTs 12
 - of synthesized AgSeTe NWs 188, 188
 - of tellurium nanosheets 174
 - of tellurium nanotubes 173
 - of tellurium NPs 170
 - of tellurium NWs 179
 - of Te nanoseeds 171
- 1,3,5-triethynylbenzene (TEB) 17
- tunneling field effect transistors (TFETs) 80
- two-dimensional materials (2DM) 1
- type A gold catalysts 49–50
- type B low Si solubility catalysts 50–51
- type C silicide-forming catalysts 51
- v**
- van der Waals (vdW) forces 4, 139, 169
 - epitaxy of 2D materials 177
 - heterojunction 153
- vapor–liquid–solid (VLS) growth
 - mechanism 41, 42, 199
 - Ag-catalyzed 50
 - Al-catalyzed 50
 - catalysts 47–51
 - of CNTs 13
 - fundamental aspects of 43
 - gold-catalyzed 52

- vapor–liquid–solid (VLS) growth
 - mechanism (*continued*)
 - growth for Ge NWs preparation 112
 - morphology analysis for 51–54
 - patterning metal NPs process 44–45
 - precursor states in heat pipes 55–57
 - schematic diagram of 43
 - silicon transportation process 45–46
 - Sn-catalyzed 51
 - vapor-phase deposition 175, 199, 211
 - vapor–solid–solid (VSS) growth
 - mechanism 12, 13, 41, 42
 - Al-catalyzed 50
 - growth of CNTs 13
 - morphology analysis for 51–54
 - schematic diagram of 43
 - for Si NWs preparation 41, 42
 - vertical GAA SNWT 88–89, 89
 - vertically stacked multi-NWs by etching 91–94
 - violet phosphorus 160–161
- W**
- white phosphorus 139

